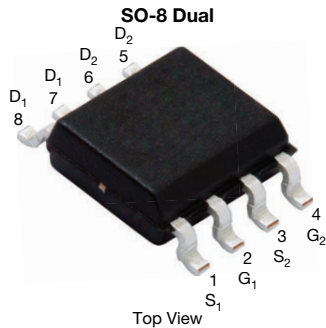


## N- and P-Channel 60 V (D-S) MOSFET



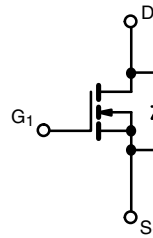
### FEATURES

- TrenchFET® Gen IV power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

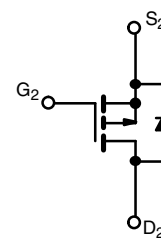


### APPLICATIONS

- CCFL Inverter
- FAN control
- Load switch



N-Channel MOSFET



P-Channel MOSFET

PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
V <sub>DS</sub> (V)	60	-60
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = ± 10 V	0.029	0.120
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = ± 4.5 V	0.038	0.150
Q <sub>g</sub> typ. (nC)	3.3	8
I <sub>D</sub> (A) <sup>a</sup>	8	-4.1
Configuration	N- and p-pair	

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	Si4534DY-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT	
Drain-source voltage	V <sub>DS</sub>	60	-60	V	
Gate-source voltage	V <sub>GS</sub>	± 20	± 20		
Continuous drain current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	8 <sup>a</sup>	-4.1	A
		T <sub>C</sub> = 70 °C	6.6	-3.3	
		T <sub>A</sub> = 25 °C	6.2 <sup>b, c</sup>	-3 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	5 <sup>b, c</sup>	-2.4 <sup>b, c</sup>	
Pulsed drain current (10 μs pulse width)	I <sub>DM</sub>	32	-25		
Source drain current diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	3	3	
		T <sub>A</sub> = 25 °C	1.7 <sup>b, c</sup>	-1.7 <sup>b, c</sup>	
Single pulse avalanche current	I <sub>AS</sub>	10	15	mJ	
Single pulse avalanche energy	E <sub>AS</sub>	5	11		
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.6	3.6	W
		T <sub>C</sub> = 70 °C	2.3	2.3	
		T <sub>A</sub> = 25 °C	2 <sup>b, c</sup>	2 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.3 <sup>b, c</sup>	1.3 <sup>b, c</sup>	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C	

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	N-CHANNEL		P-CHANNEL		UNIT	
		TYP.	MAX.	TYP.	MAX.		
Maximum junction-to-ambient <sup>b, d</sup>	t ≤ 10 s	R <sub>thJA</sub>	50	62.5	50	62.5	°C/W
Maximum junction-to-foot (drain)	Steady state	R <sub>thJF</sub>	28	35	27	34	

#### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- Maximum under steady state conditions is 110 °C/W for N-channel and P-channel



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. <sup>a</sup>	MAX.	UNIT			
<b>Static</b>									
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	N-Ch	60	-	-	V		
		V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	P-Ch	-60	-	-			
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	N-Ch	-	33	-	mV		
		I <sub>D</sub> = -250 μA	P-Ch	-	50	-			
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	N-Ch	-	-4.8	-	mV		
		I <sub>D</sub> = -250 μA	P-Ch	-	4	-			
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	N-Ch	1	-	3	V		
		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	P-Ch	-1	-	-3			
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	N-Ch	-	-	100	nA		
			P-Ch	-	-	-100			
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	N-Ch	-	-	1	μA		
		V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V	P-Ch	-	-	-1			
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	N-Ch	-	-	15			
		V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	P-Ch	-	-	-15			
Drain-source on-state resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A	N-Ch	-	0.022	0.029	Ω		
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.1 A	P-Ch	-	0.100	0.120			
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4 A	N-Ch	-	0.029	0.038			
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.2 A	P-Ch	-	0.126	0.150			
Forward transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A	N-Ch	-	23	-	S		
		V <sub>DS</sub> = -15 V, I <sub>D</sub> = -3.1 A	P-Ch	-	8.5	-			
<b>Dynamic <sup>a</sup></b>									
Input capacitance	C <sub>iss</sub>	N-channel V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz  P-channel V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	N-Ch	-	420	-	pF		
			P-Ch	-	650	-			
Output capacitance	C <sub>oss</sub>		N-Ch	-	92	-			
			P-Ch	-	95	-			
Reverse transfer capacitance	C <sub>rss</sub>		N-Ch	-	4	-			
			P-Ch	-	60	-			
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A	N-Ch	-	7.1	11	nC		
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.1 A	P-Ch	-	14.5	22			
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A	N-Ch	-	3.3	5			
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.1 A	P-Ch	-	8	12			
Gate-source charge	Q <sub>gs</sub>	N-channel V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A  P-channel V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.1 A	N-Ch	-	1.7	-	nC		
			P-Ch	-	2.2	-			
Gate-drain charge	Q <sub>gd</sub>		N-Ch	-	0.9	-			
			P-Ch	-	3.7	-			
Gate resistance	R <sub>g</sub>		f = 1 MHz	N-Ch	0.3	1.6		3.2	Ω
				P-Ch	3	14		28	



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. <sup>a</sup>	MAX.	UNIT	
<b>Dynamic <sup>a</sup></b>							
Turn-on delay time	t <sub>d(on)</sub>	N-channel V <sub>DD</sub> = 30 V, R <sub>L</sub> = 6 Ω, I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	N-Ch	-	12	25	ns
Rise time	t <sub>r</sub>		P-Ch	-	30	60	
Turn-off delay time	t <sub>d(off)</sub>	P-channel V <sub>DD</sub> = -30 V, R <sub>L</sub> = 12.5 Ω, I <sub>D</sub> ≅ -2.4 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω	N-Ch	-	16	35	
			P-Ch	-	70	140	
Fall time	t <sub>f</sub>		N-Ch	-	11	25	
			P-Ch	-	40	80	
Turn-on delay time	t <sub>d(on)</sub>	N-channel V <sub>DD</sub> = 30 V, R <sub>L</sub> = 6 Ω, I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	N-Ch	-	5	10	
			P-Ch	-	30	60	
Rise time	t <sub>r</sub>		N-Ch	-	10	20	
			P-Ch	-	10	20	
Turn-off delay time	t <sub>d(off)</sub>	P-channel V <sub>DD</sub> = -30 V, R <sub>L</sub> = 12.5 Ω, I <sub>D</sub> ≅ -2.4 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω	N-Ch	-	5	10	
			P-Ch	-	13	25	
Fall time	t <sub>f</sub>		N-Ch	-	15	30	
			P-Ch	-	35	70	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	N-Ch	-	-	8	A
			P-Ch	-	-	-2.8	
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>		N-Ch	-	-	32	
			P-Ch	-	-	-25	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 2 A	N-Ch	-	0.8	1.2	V
		I <sub>S</sub> = -2 A	P-Ch	-	-0.8	-1.2	
Body diode reverse recovery time	t <sub>rr</sub>	N-channel I <sub>F</sub> = 5 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	N-Ch	-	14	30	ns
			P-Ch	-	30	50	
Body diode reverse recovery charge	Q <sub>rr</sub>		N-Ch	-	10	20	nC
			P-Ch	-	35	60	
Reverse recovery fall time	t <sub>a</sub>	P-channel I <sub>F</sub> = -2 A, di/dt = -100 A/μs, T <sub>J</sub> = 25 °C	N-Ch	-	8	-	ns
			P-Ch	-	16	-	
Reverse recovery rise time	t <sub>b</sub>		N-Ch	-	6	-	
			P-Ch	-	14	-	

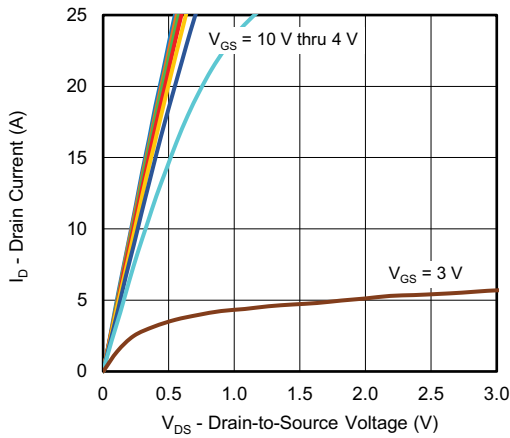
**Notes**

- a. Guaranteed by design, not subject to production testing
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2

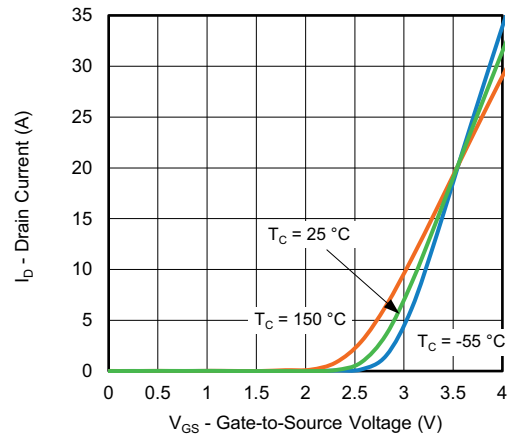
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



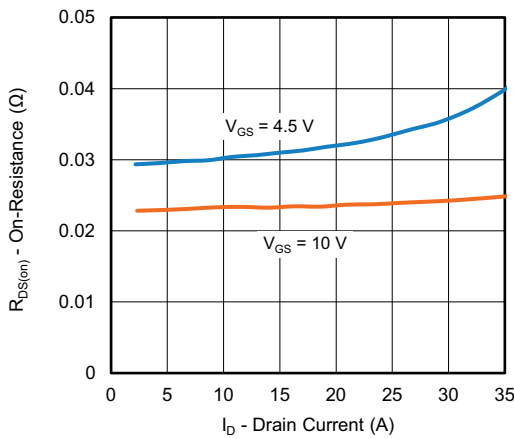
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



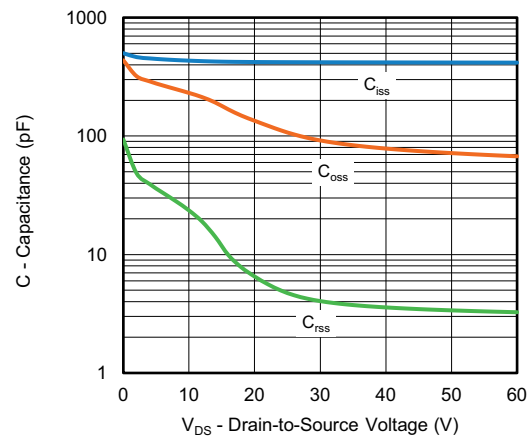
Output Characteristics



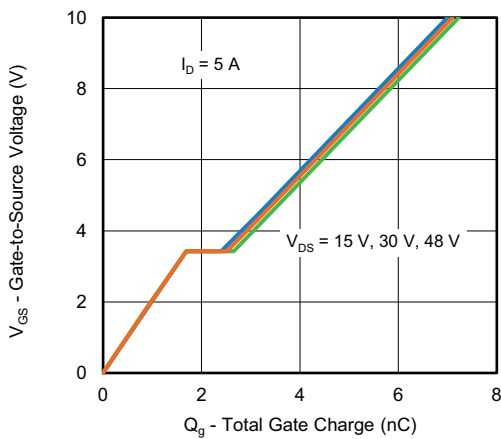
Transfer Characteristics



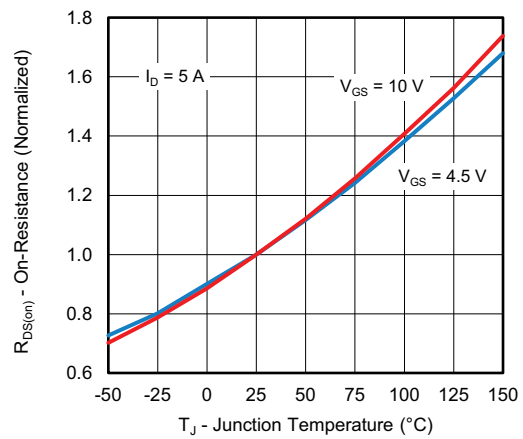
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



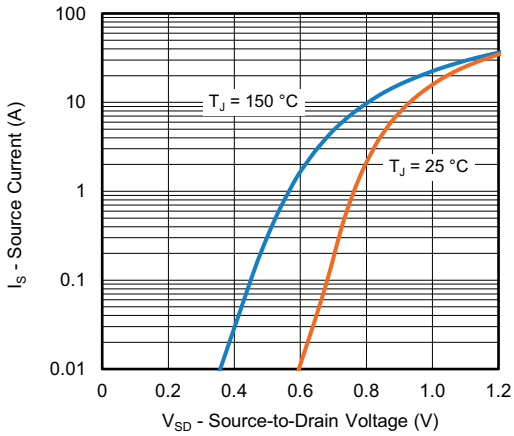
Gate Charge



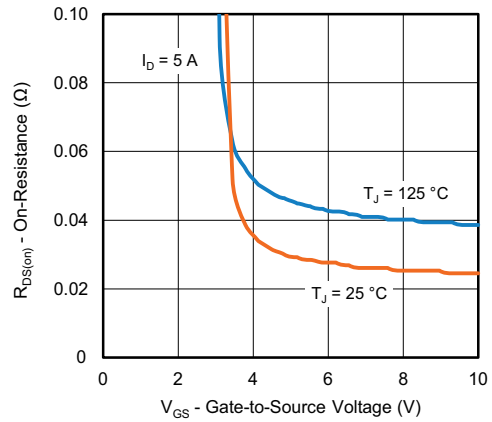
On-Resistance vs. Junction Temperature



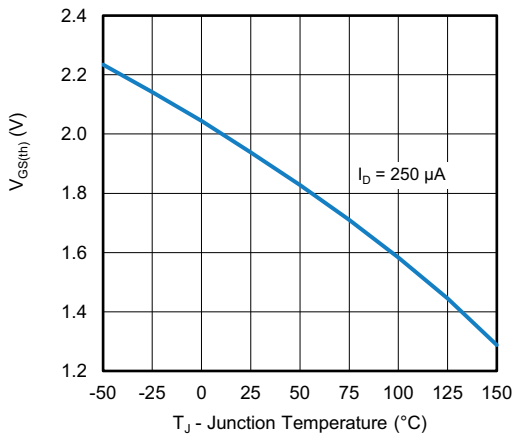
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



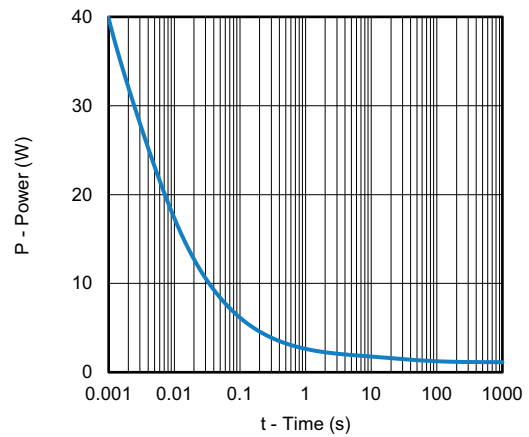
Source-Drain Diode Forward Voltage



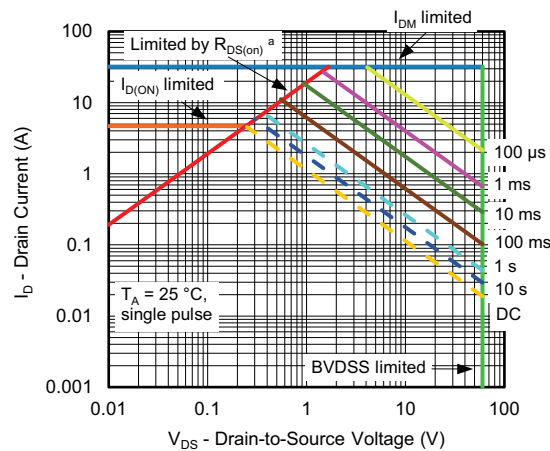
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



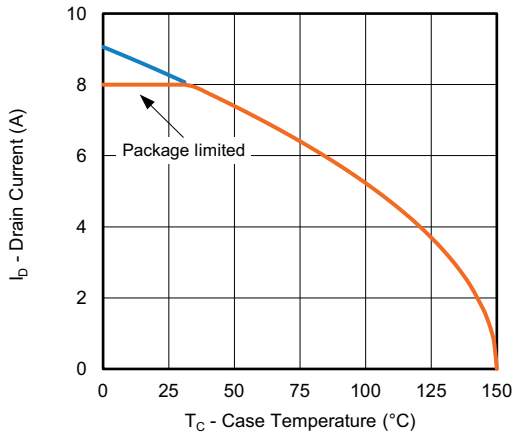
Single Pulse Power, Junction-to-Ambient



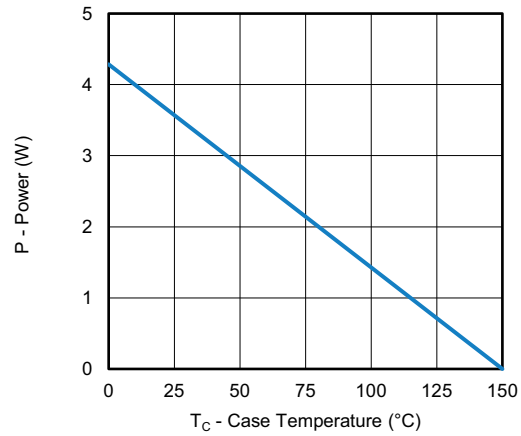
Safe Operating Area



**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



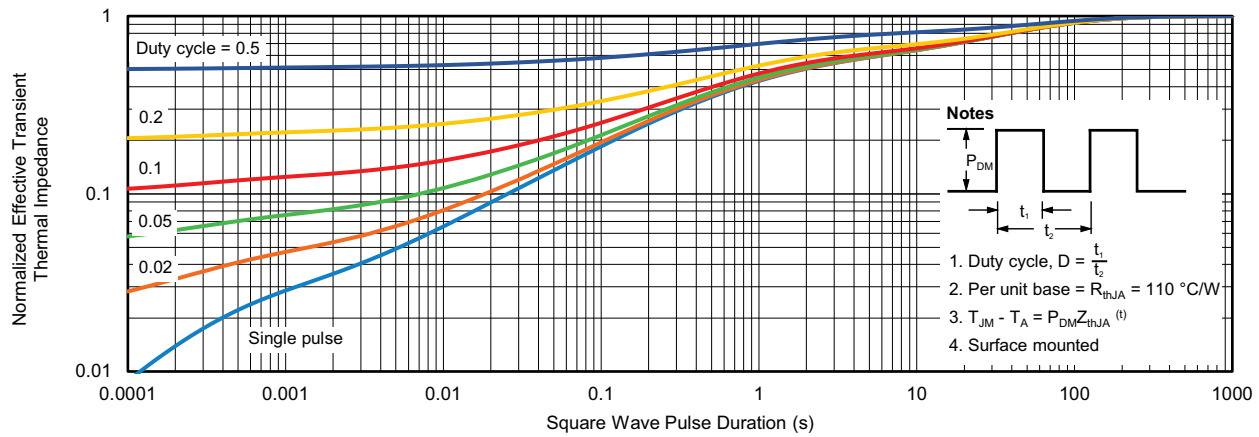
**Power Derating**

**Note**

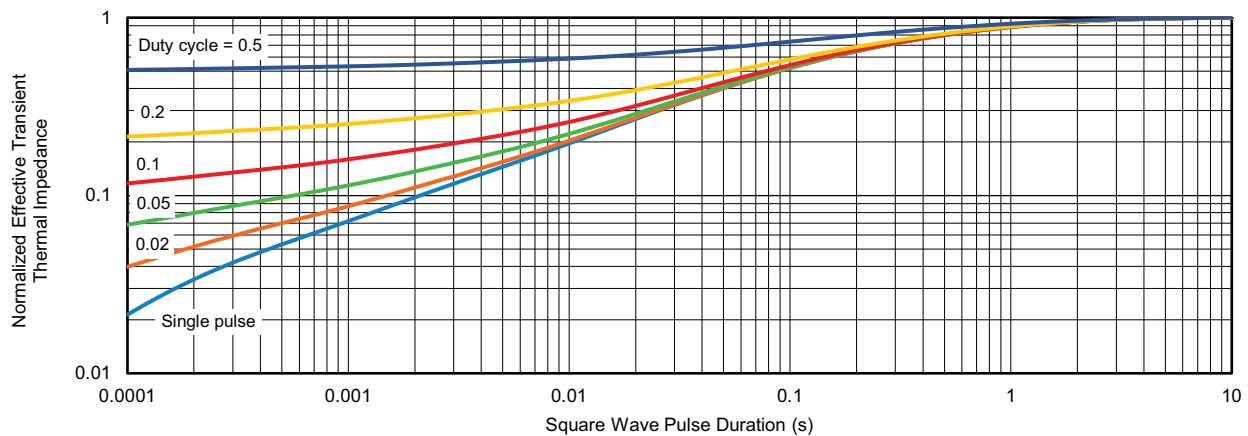
- a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



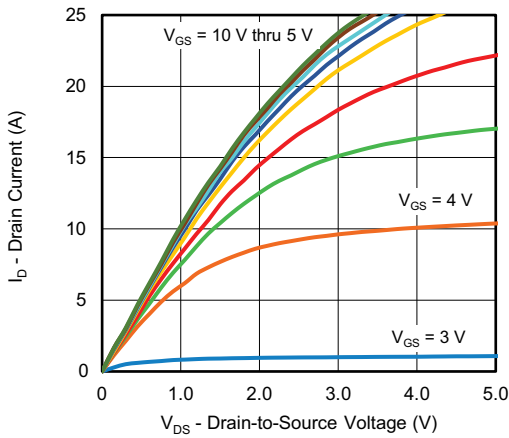
Normalized Thermal Transient Impedance, Junction-to-Ambient



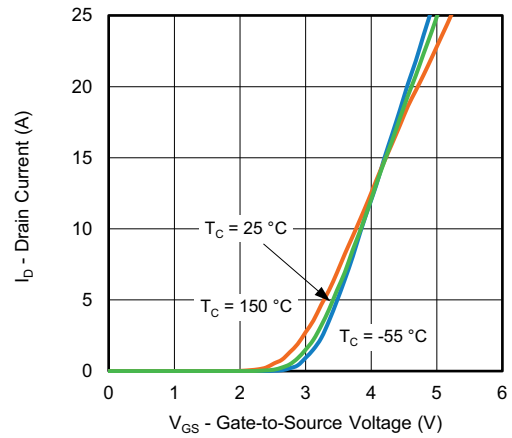
Normalized Thermal Transient Impedance, Junction-to-Case



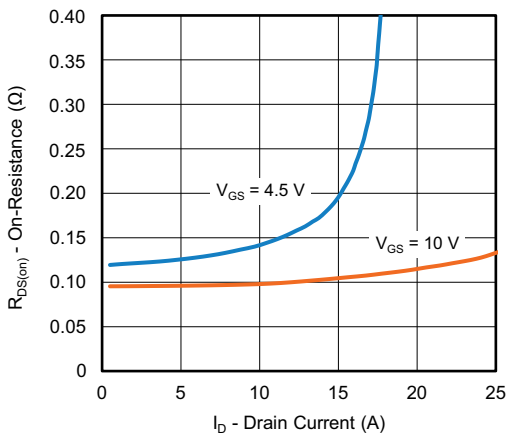
**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



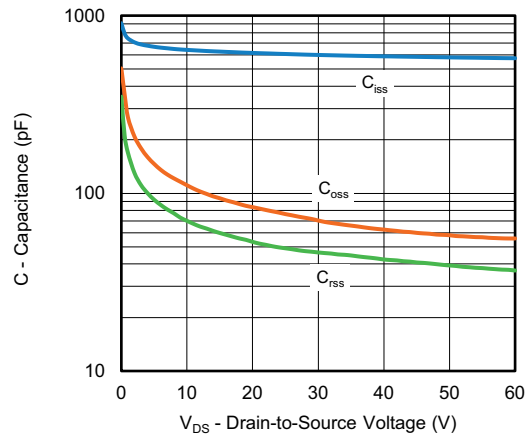
**Output Characteristics**



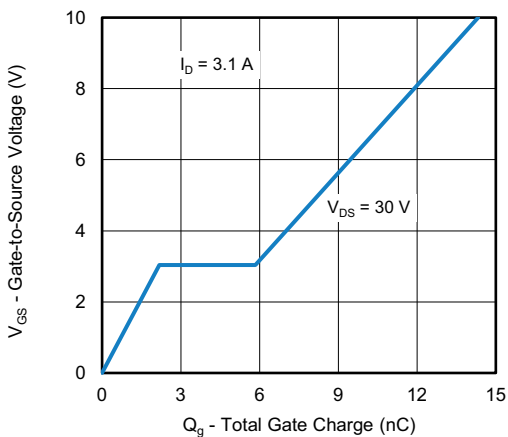
**Transfer Characteristics**



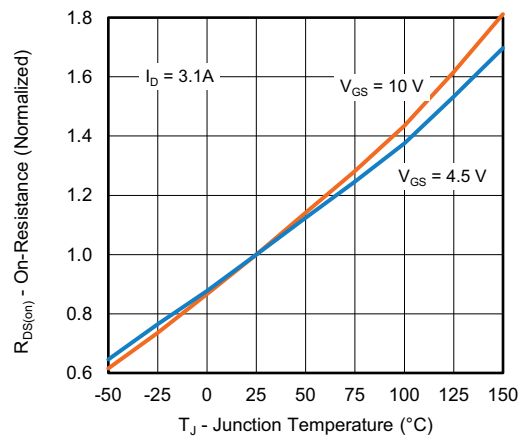
**On-Resistance vs. Drain Current**



**Capacitance**



**Gate Charge**

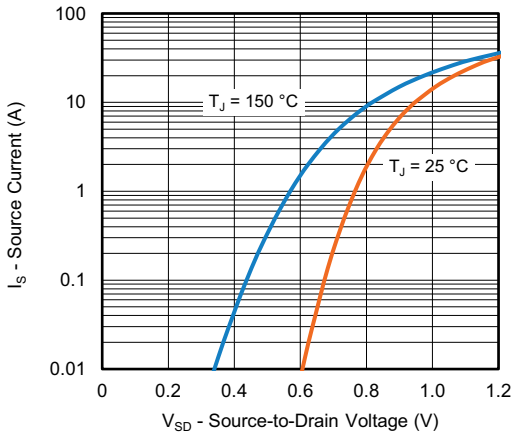


**On-Resistance vs. Junction Temperature**

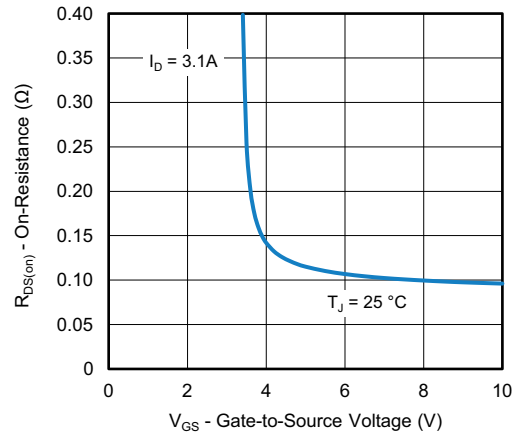




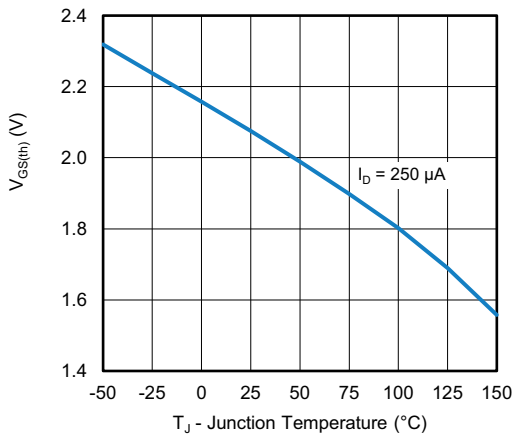
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



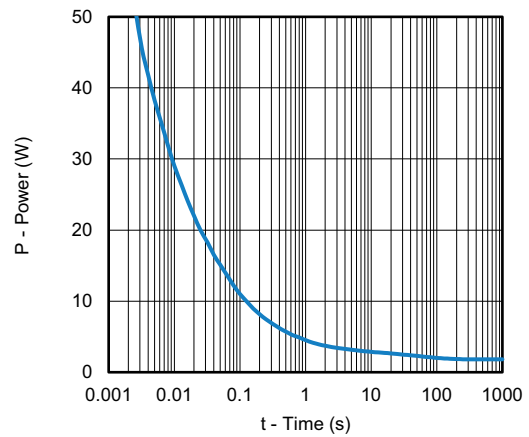
Source-Drain Diode Forward Voltage



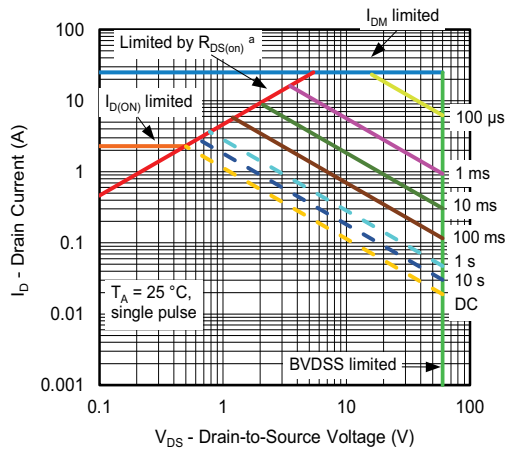
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



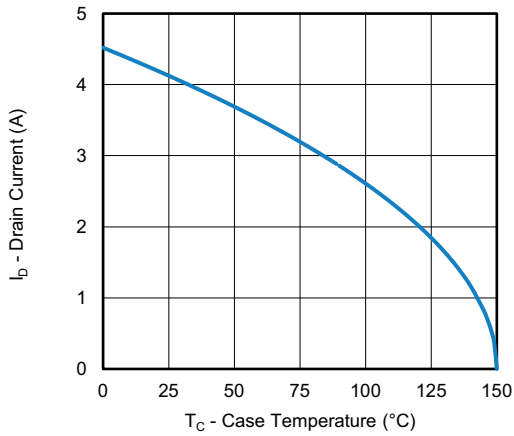
Single Pulse Power



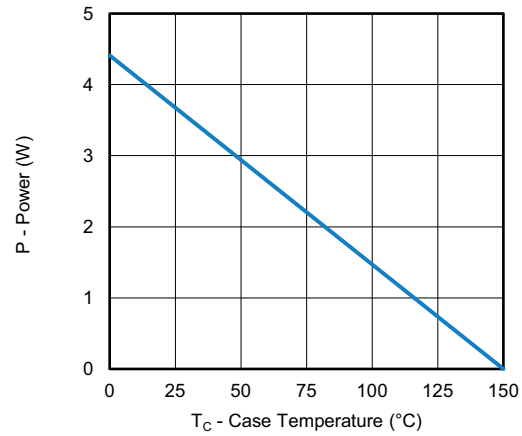
Safe Operating Area, Junction-to-Case



**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



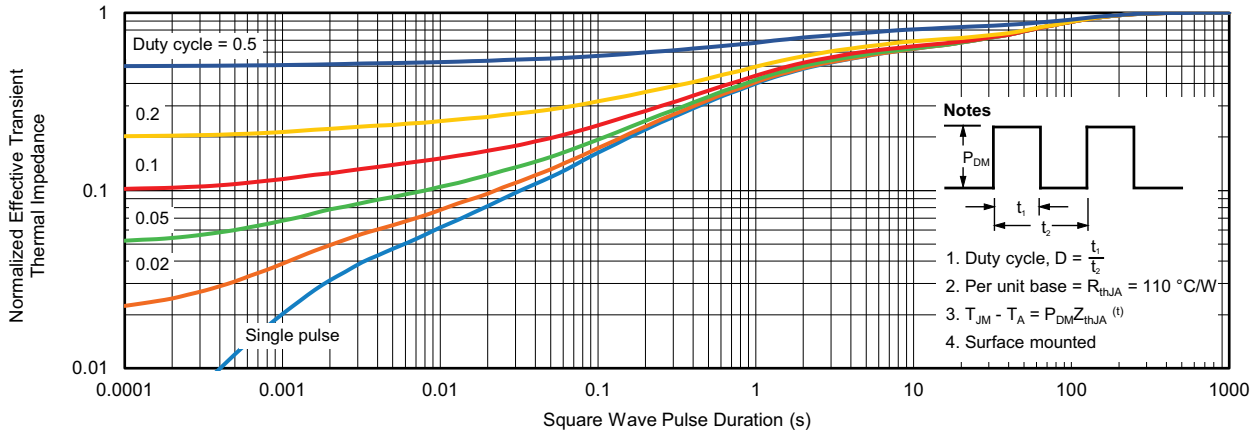
**Power Derating, Junction-to-Foot**

**Note**

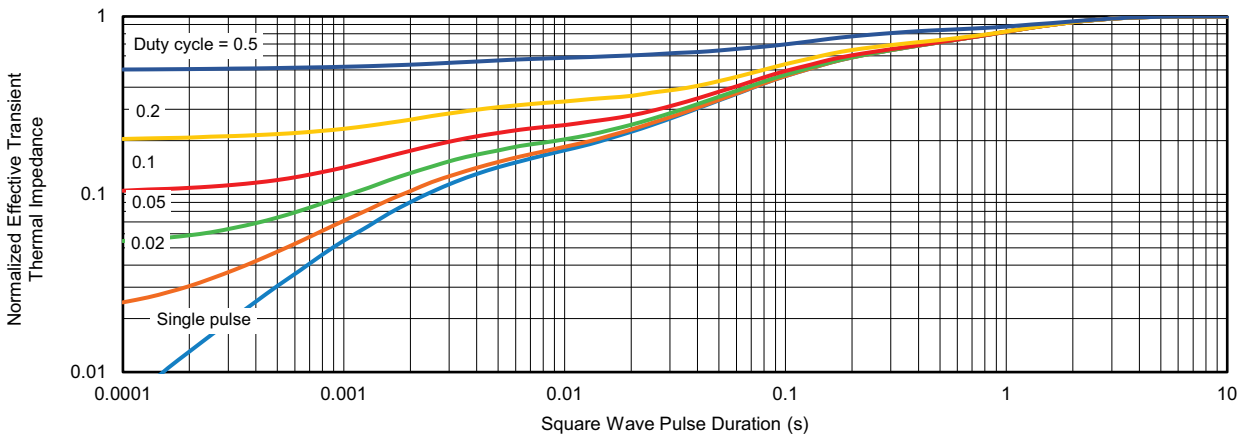
- a. The power dissipation  $P_D$  is based on  $T_J$  max = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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